Silicon N Channel MOS FET High Speed Power Switching

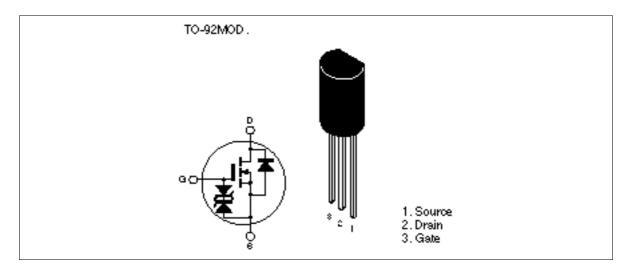


ADE-208-520 1st. Edition

#### Features

- Low on-resistance  $R_{DS(on)}=0.04\Omega \mbox{ typ (at } V_{GS}=10 \mbox{ V}, \mbox{ } I_{D}=2.5 \mbox{ A})$
- 4V gate drive devices.
- Large current capacitance  $I_D = 5 A$

#### Outline





#### **Absolute Maximum Ratings** (Ta = $25^{\circ}$ C)

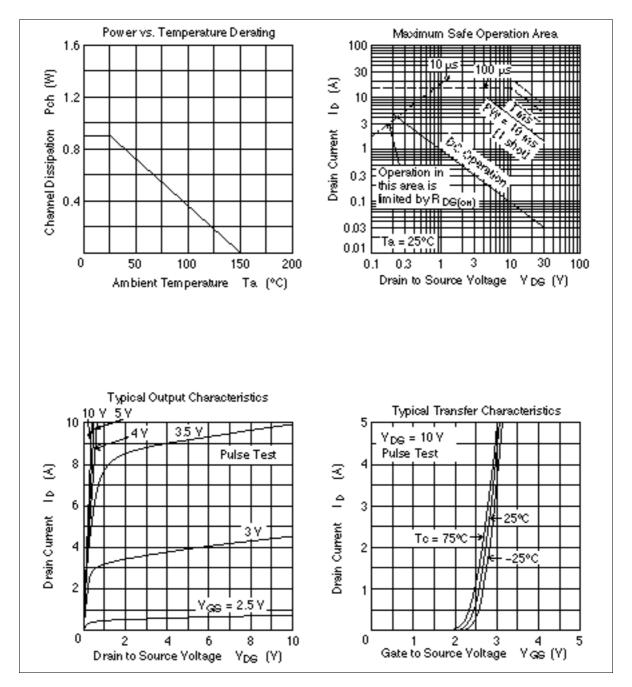
Item	Symbol	Ratings	Unit	
Drain to source voltage	V <sub>DSS</sub>	30	V	
Gate to source voltage	V <sub>GSS</sub>	±20	V	
Drain current	ID	5	А	
Drain peak current	I <sub>D(pulse)</sub> * <sup>1</sup>	20	А	
Body to drain diode reverse drain current	I <sub>DR</sub>	5	А	
Channel dissipation	Pch	0.9	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Note: 1.  $PW \le 10\mu s$ , duty cycle  $\le 1 \%$ 

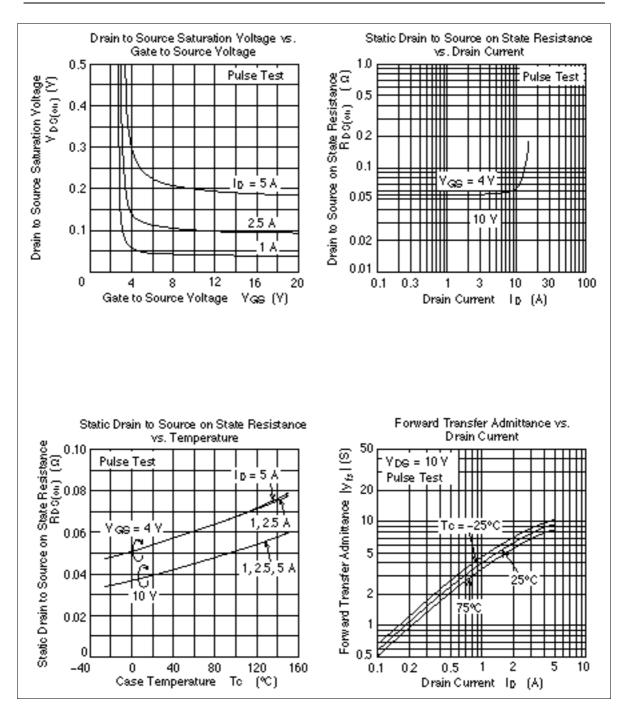
#### **Electrical Characteristics** (Ta = 25°C)

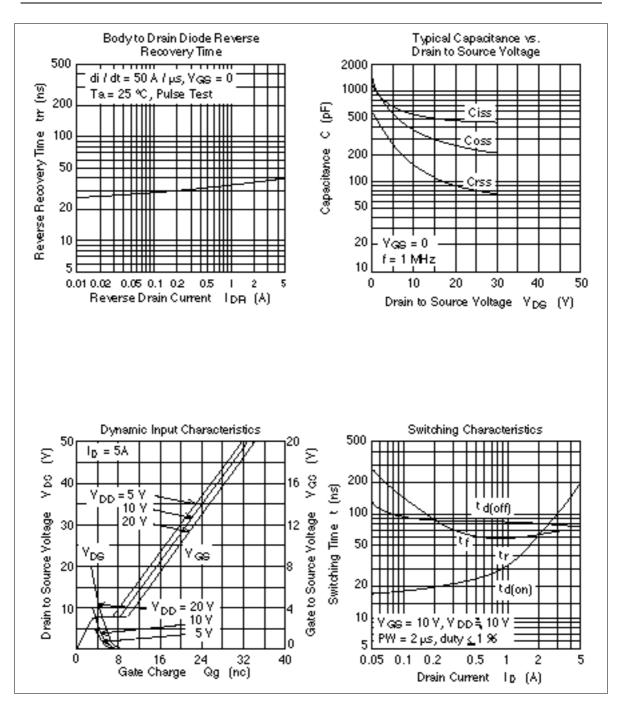
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	_	V	$I_{D} = 10 mA, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	_	V	$I_G = \pm 100 \mu A, V_{DS} = 0$
Zero gate voltege drain current	I <sub>DSS</sub>			10	μA	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>			±10	μA	$V_{GS} = \pm 16V, V_{DS} = 0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	1.0		2.0	V	$I_D = 1mA$ , $V_{DS} = 10V$
Static drain to source on state	R <sub>DS(on)</sub>	_	0.04	0.055	Ω	$I_D = 2.5A, V_{GS} = 10V^{*1}$
resistance	R <sub>DS(on)</sub>	_	0.055	0.08	Ω	$I_D = 2.5A, V_{GS} = 4V^{*1}$
Forward transfer admittance	y <sub>fs</sub>	4	7		S	$I_D = 2.5A, V_{DS} = 10V^{*1}$
Input capacitance	Ciss	_	550	_	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss		380		pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss		155		pF	f = 1MHz
Turn-on delay time	t <sub>d(on)</sub>	_	14	_	ns	$V_{GS} = 10V, I_D = 2.5A$
Rise time	tr	_	80	_	ns	$R_L = 4\Omega$
Turn-off delay time	t <sub>d(off)</sub>	_	80	_	ns	
Fall time	t <sub>f</sub>	_	65	_	ns	
Body to drain diode forward voltage	$V_{DF}$	_	1.0	_	V	$I_D = 5A, V_{GS} = 0$
Body to drain diode reverse recovery time	t <sub>rr</sub>	—	40	—	ns	$I_F = 5A$ , $V_{GS} = 0$ di <sub>F</sub> / dt = 50A/µs
Note: 1. Pulse test						

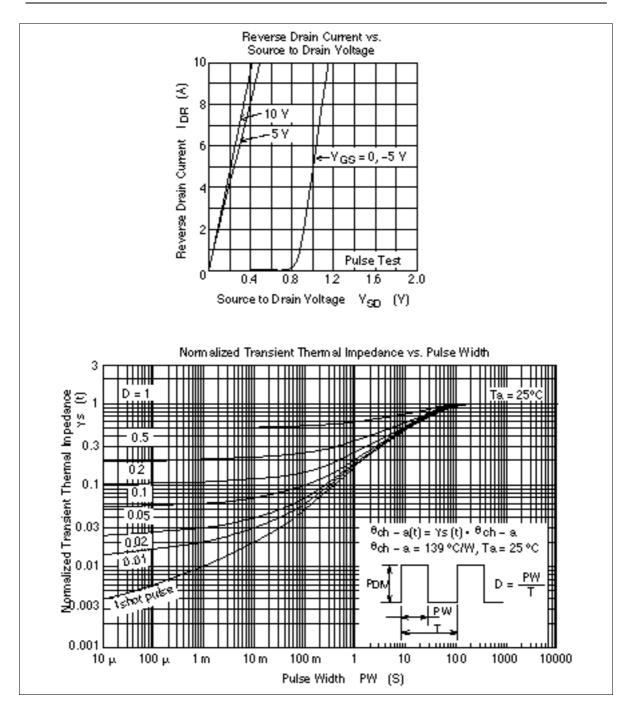
Note: 1. Pulse test

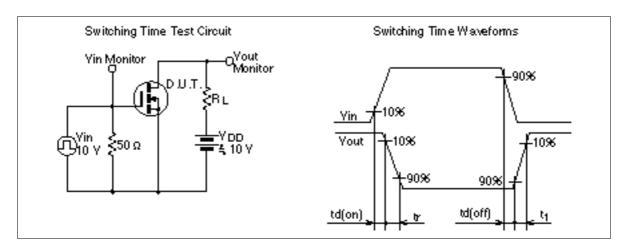


#### **Main Characteristics**

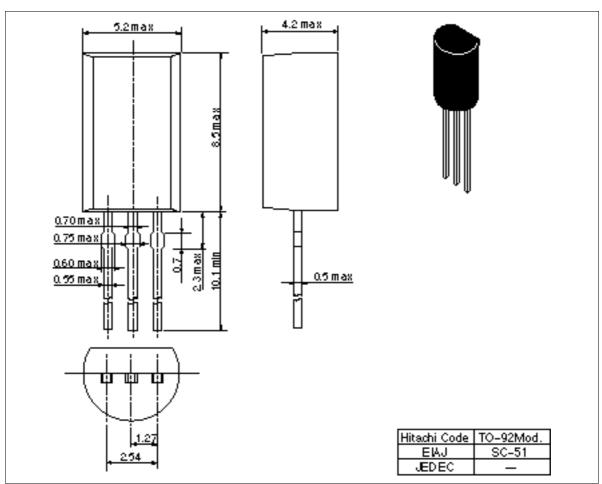








## **Package Dimentions**



Unit: mm

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